

isc Silicon NPN Power Transistor

2SC3885

DESCRIPTION

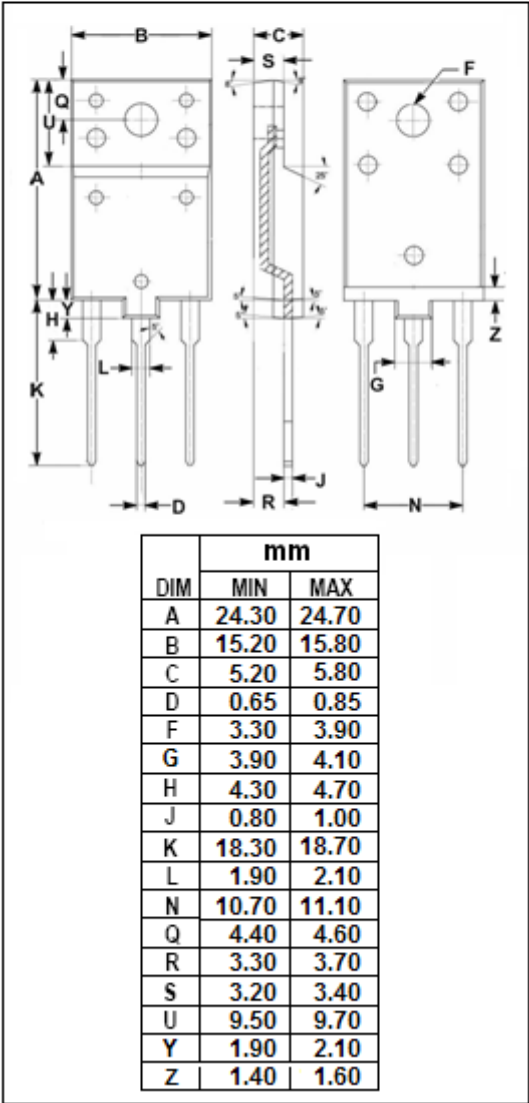
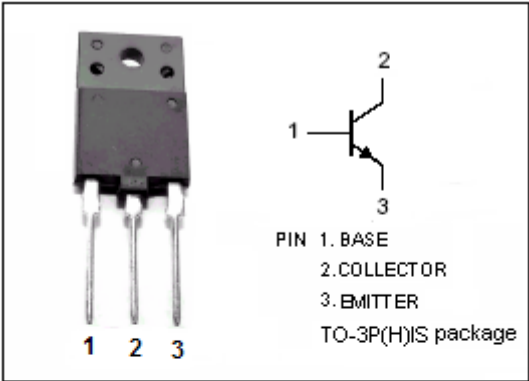
- High Breakdown Voltage-
: $V_{CBO}=1400V$ (Min)
- High Switching Speed

APPLICATIONS

- Horizontal deflection output for high resolution display.
- High speed switching regulator output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1400	V
V_{CEO}	Collector-Emitter Voltage	600	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	7	A
I_{CM}	Collector Current- Peak	14	A
I_B	Base Current- Continuous	3.5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



ISC Silicon NPN Power Transistor**2SC3885****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA; I _B = 0	600			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1.2A			5.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1.2A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 1400V; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μ A
h _{FE}	DC Current Gain	I _C = 1A; V _{CE} = 5V	8			
f _T	Current-Gain—Bandwidth Product	I _C = 0.1A; V _{CE} = 10V		3		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		210		pF

Switching Times , Resistive load

t _{stg}	Storage Time	I _{CP} = 5A, I _{B1} = 1A; I _{B2} = -2A; R _L = 40 Ω			2.5	μ s
t _f	Fall Time				0.15	μ s